

Tetsuo Hatakeyama

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

20
papers

343
citations

8
h-index

18
g-index

20
ext. papers

386
ext. citations

2.2
avg, IF

2.54
L-index

| # | Paper | IF | Citations |
|----|---|-----|-----------|
| 20 | Impact ionization coefficients of 4H silicon carbide. <i>Applied Physics Letters</i> , 2004 , 85, 1380-1382 | 3.4 | 95 |
| 19 | Dependence of acceptor levels and hole mobility on acceptor density and temperature in Al-doped p-type 4H-SiC epilayers. <i>Journal of Applied Physics</i> , 2004 , 96, 2708-2715 | 2.5 | 69 |
| 18 | Parameters required to simulate electric characteristics of SiC devices for n-type 4H-BiC. <i>Journal of Applied Physics</i> , 2004 , 96, 5601-5606 | 2.5 | 57 |
| 17 | Ultralow-Loss SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 1954-1960 | 2.9 | 23 |
| 16 | Electronic properties of a Penrose tiling lattice in a magnetic field. <i>Solid State Communications</i> , 1987 , 62, 79-83 | 1.6 | 20 |
| 15 | Ideal phonon-scattering-limited mobility in inversion channels of 4H-SiC(0001) MOSFETs with ultralow net doping concentrations. <i>Applied Physics Letters</i> , 2019 , 115, 132102 | 3.4 | 12 |
| 14 | Impact of crystal faces of 4H-SiC in SiO ₂ /4H-SiC structures on interface trap densities and mobilities. <i>Applied Physics Express</i> , 2019 , 12, 021003 | 2.4 | 12 |
| 13 | Fractal Nature of the Electronic Structure of a Penrose Tiling Lattice in a Magnetic Field. <i>Journal of the Physical Society of Japan</i> , 1989 , 58, 260-268 | 1.5 | 10 |
| 12 | Characterization of traps in SiC/SiO ₂ interfaces close to the conduction band by deep-level transient spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 111301 | 1.4 | 8 |
| 11 | Mobility modulation of two-dimensional hole gas in a p-type Si/SiGe modulation doped heterostructure by back-gating. <i>Semiconductor Science and Technology</i> , 1998 , 13, 1477-1479 | 1.8 | 7 |
| 10 | Mobility-limiting Coulomb scattering in nitrided 4H-SiC inversion channel on 1 1 00 m-face and 11 2 00 a-face characterized by Hall effect measurements. <i>Applied Physics Letters</i> , 2019 , 115, 132106 | 3.4 | 5 |
| 9 | Electrically detected-magnetic-resonance identifications of defects at 4H-SiC(000 1 0)/SiO ₂ interfaces with wet oxidation. <i>Applied Physics Letters</i> , 2019 , 115, 151602 | 3.4 | 5 |
| 8 | Evaluation of the quality of commercial silicon carbide wafers by an optical non-destructive inspection technique. <i>Journal of Crystal Growth</i> , 2008 , 310, 988-992 | 1.6 | 5 |
| 7 | Surface defects generated by extrinsic origins on 4H-SiC epitaxial-wafers observed by scanning electron microscopy. <i>Microscopy (Oxford, England)</i> , 2017 , 66, 103-109 | 1.3 | 4 |
| 6 | Difference in electron mobility at 4H-BiC/SiO ₂ interfaces with various crystal faces originating from effective-field-dependent scattering. <i>Applied Physics Letters</i> , 2020 , 117, 042101 | 3.4 | 4 |
| 5 | Pragmatic Approach to the Characterization of SiC/SiO ₂ Interface Traps near the Conduction Band with Split C-V and Hall Measurements. <i>Materials Science Forum</i> , 2016 , 858, 477-480 | 0.4 | 3 |
| 4 | Theoretical prediction on the formation of icosahedra in quasicrystals. <i>Solid State Communications</i> , 1992 , 84, 227-229 | 1.6 | 3 |

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| 3 | Localization in hybridized Fibonacci quasi- crystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1992 , 14, L5-L9 | 3.1 | 1 |
| 2 | Transport properties of two-dimensional electron gas in a strained-Si/SiGe heterostructure at low carrier densities. <i>Thin Solid Films</i> , 2000 , 369, 328-332 | 2.2 | |
| 1 | Dipole scattering at the interface: The origin of low mobility observed in SiC MOSFETs. <i>Journal of Applied Physics</i> , 2022 , 131, 145701 | 2.5 | |